

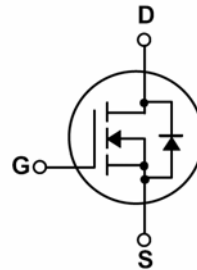
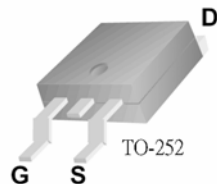
1 Description

These N-Channel enhancement mode power field effect transistors are produced using planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

2 Features

- 500V / 4.5A
- $R_{DS(on)} = 1.2\Omega(\text{typ})$, $V_{GS} = 10V$, $I_D = 2.7A$
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability..



3 Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	APQ4ESN50AB-XXM0	Units
		APQ4ESN50AB-XXM1	
		APQ4ESN50AB-XXJ1	
		TO-252	
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	4.5	A
		2.7	A
I_{DM}	Drain Current – Pulsed ①	18	A
V_{GS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	280	mJ
I_{AR}	Avalanche Current	3.5	A
E_{AR}	Repetitive Avalanche Energy	7.4	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - De-rate above 25°C	38	W
		0.3	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

* note :

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 50V$, starting $T_J = 25^\circ\text{C}$, $L = \text{TBD}$, $R_G = 25\Omega$, $I_{AS} = 4.5A$
- ③ $I_{SD} \leq 4.5A$, $di/dt \leq 100A/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.



DEVICE SPECIFICATION

APQ4ESN50AB

500V/4.5A N-Channel MOSFET

4 Thermal Characteristics

Symbol	Parameter	APQ4ESN50AB-XXM0	Units
		APQ4ESN50AB-XXM1	
		APQ4ESN50AB-XXJ1	
		TO-252	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.71	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^{\circ}\text{C/W}$

5 Electrical Characteristics $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C	--	0.61	--	$\text{V}/^{\circ}\text{C}$
I_{DSS}	Gate to Source leakage current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	20	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}$ ④	--	1.2	1.5	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 2.25\text{ A}$ ①	--	--	10	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	610	--	pF
C_{oss}	Output Capacitance		--	160	--	pF
C_{rss}	Reverse Transfer Capacitance		--	68	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 6\text{ A},$ $R_G = 25\ \Omega$ ④	--	8.2	--	ns
t_r	Turn-On Rise Time		--	16	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	42	--	ns
t_f	Turn-Off Fall Time		--	16	--	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 3.1\text{ A},$ $V_{GS} = 10\text{ V}$ ④	--	--	38	nC
Q_{gs}	Gate-Source Charge		--	--	5	nC
Q_{gd}	Gate-Drain Charge		--	--	22	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	4.5	--	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	18	--	A



DEVICE SPECIFICATION

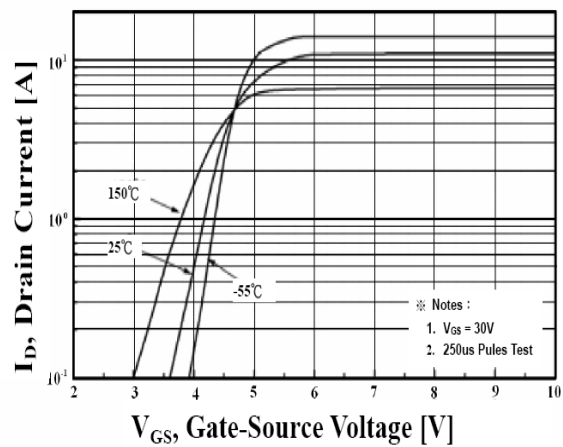
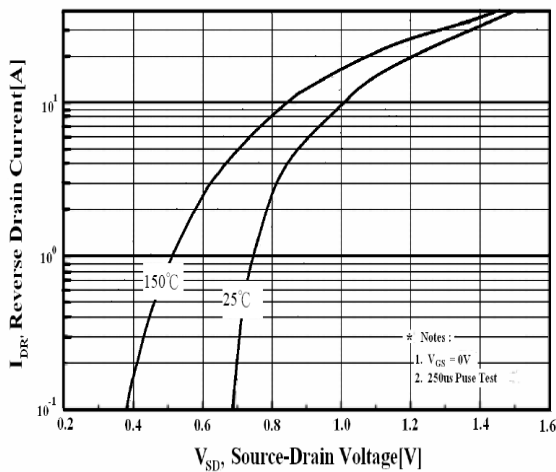
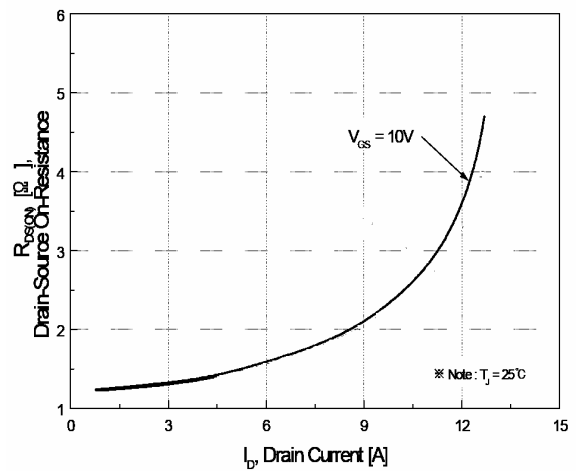
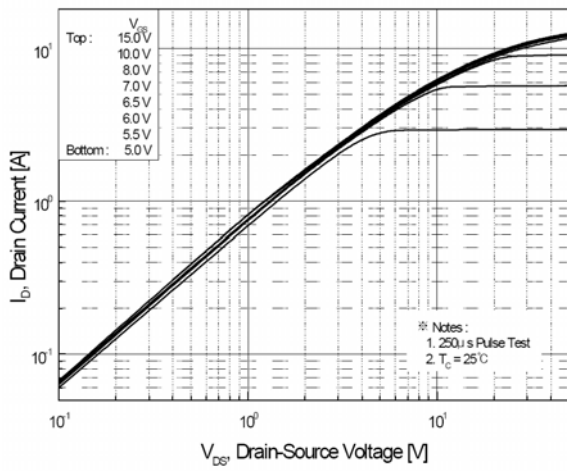
APQ4ESN50AB

500V/4.5A N-Channel MOSFET

V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 4.5\text{ A}$	--	--	1.6	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_F = 3.1\text{ A},$ $dI_F/dt = 100\text{ A}/\mu\text{s}$ ④	--	320	640	ns
Q_{rr}	Reverse Recovery Charge		--	1.0	2.0	μC

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 50\text{V}$, starting $T_J = 25^\circ\text{C}$, $L = \text{TBD}$, $R_G = 25\Omega$, $I_{AS} = 4.5\text{A}$
- ③ $I_{SD} \leq 4.5\text{A}$, $di/dt \leq 75\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ④ Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$. Depend on FT Test.
- ⑤ CP Test

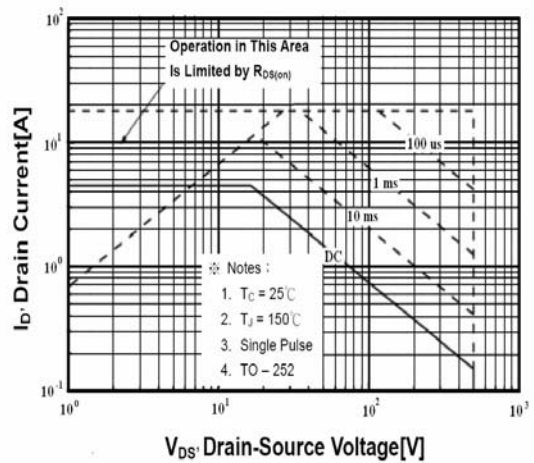
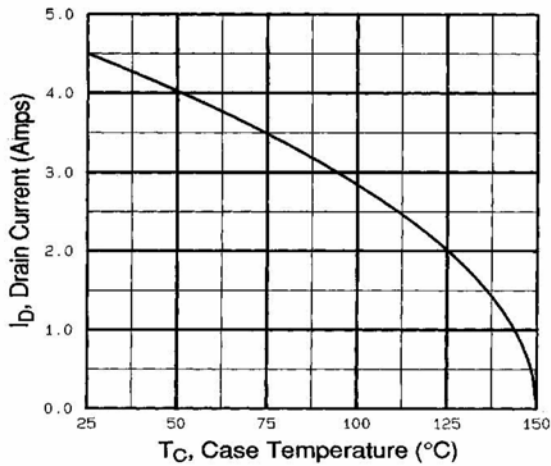
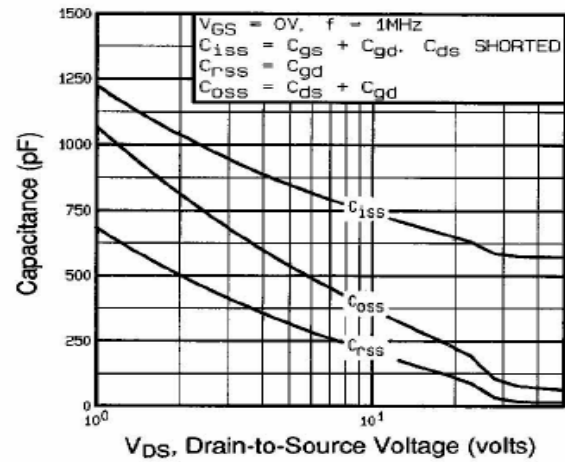
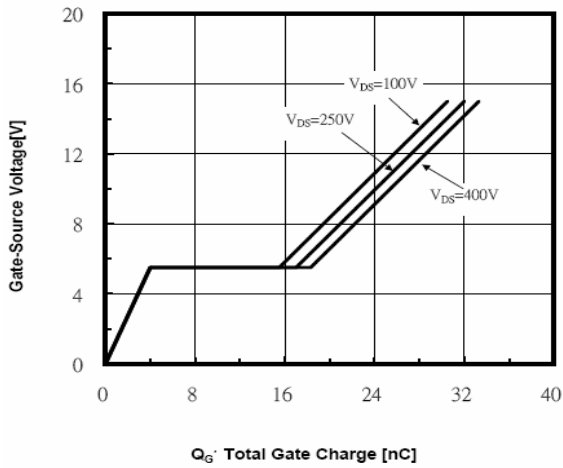
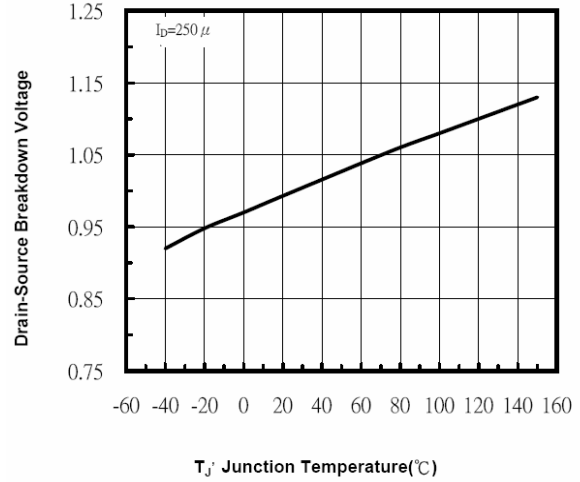
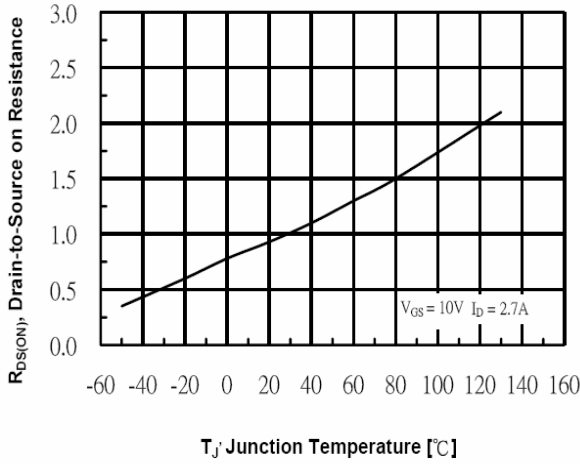


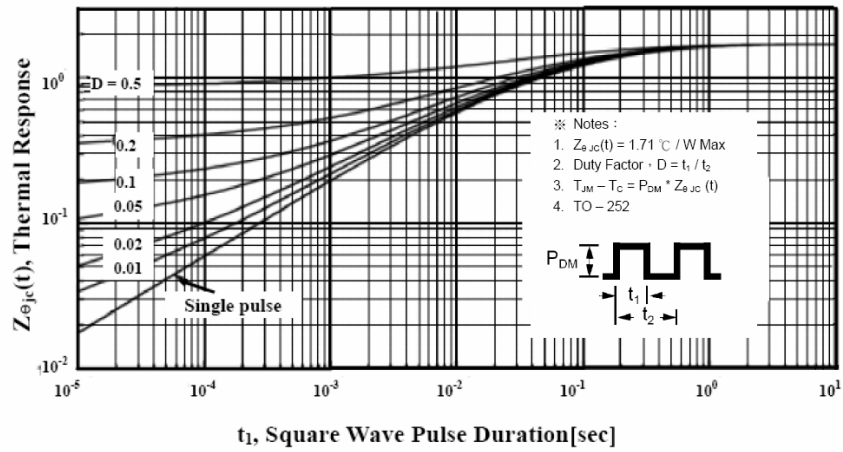


DEVICE SPECIFICATION

APQ4ESN50AB

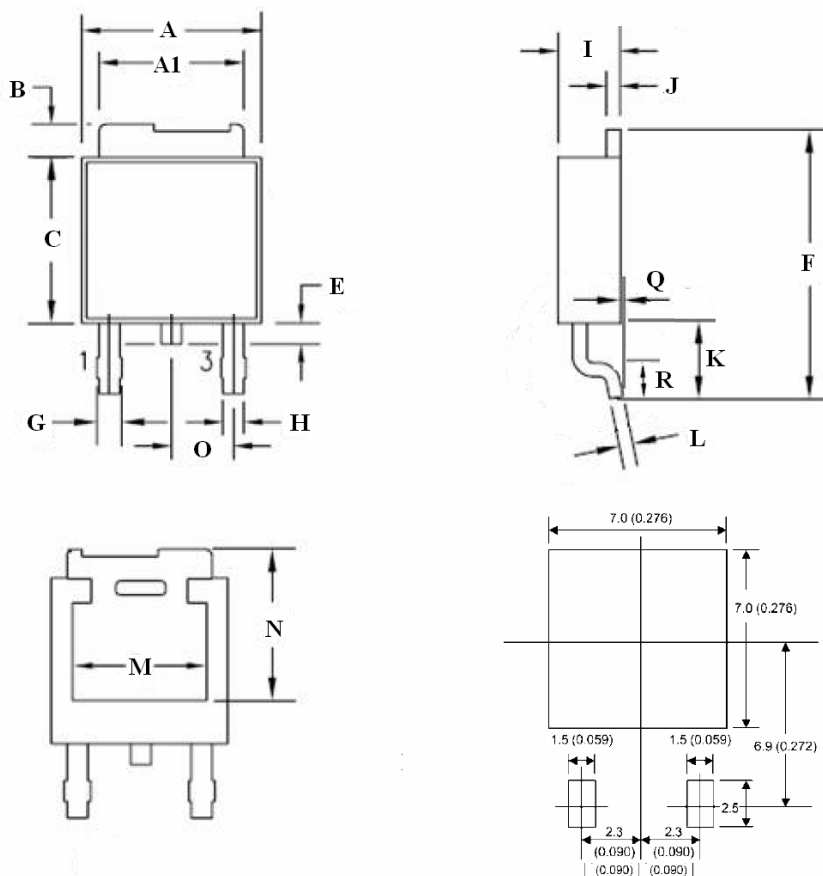
500V/4.5A N-Channel MOSFET





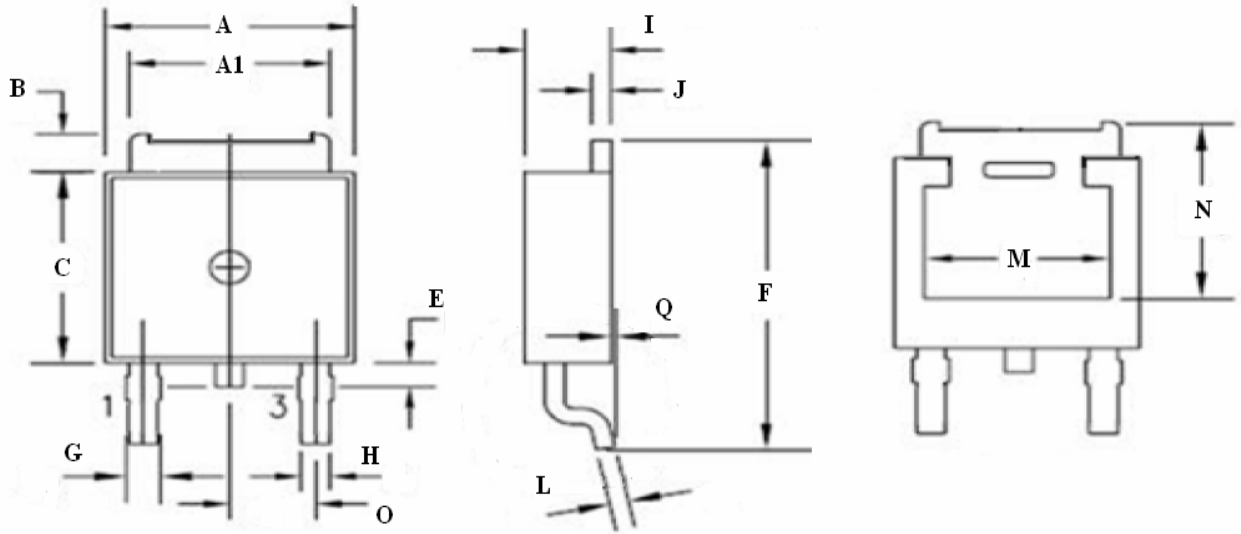
6 Package Dimensions

APQ4ES50AB-XXM0
TO-252



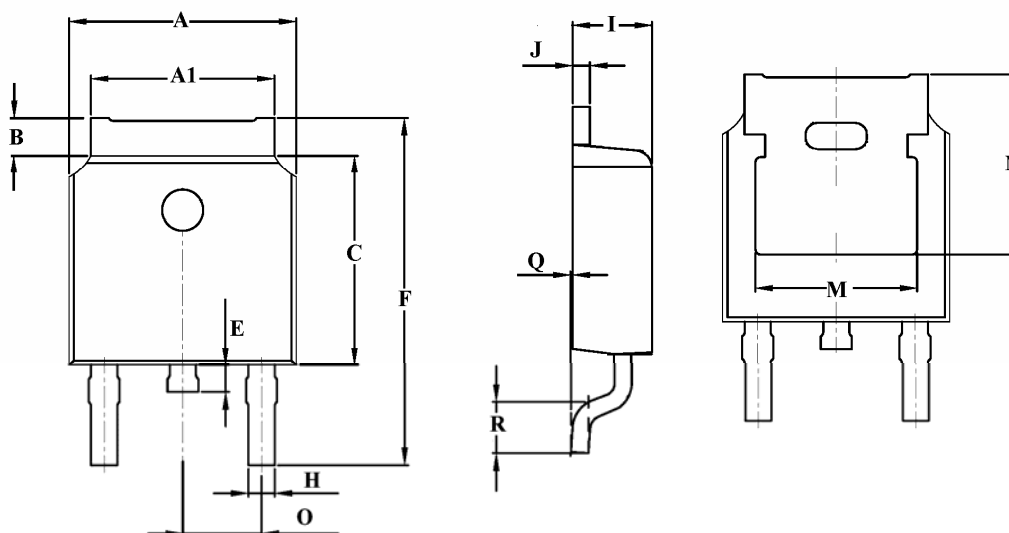
TO-252DIMENSION							
DIM	MILLIMETERS						
	MIN	MAX	TYP.	DIM	MIN	MAX	TYP.
A	6.35	6.73	6.54	J	0.46	0.61	0.535
A1	5.21	5.46	5.335	K	2.550	2.900	2.725
B	0.89	1.27	1.08	L	0.46	0.61	0.535
C	5.97	6.22	6.095	M	4.83	--	
E	0.64	1.01	0.825	N	5.21	--	
F	9.65	10.14	9.895	O	2.29 BSC		
G	0.84	1.14	0.99	P	0.51 BSC		
H	0.64	0.89	0.765	Q	0	0.130	0.065
I	2.19	2.38	2.285	R	1.40	1.780	1.590

APQ4ESN50AB-XXM1
TO-252



TO-252DIMENSION							
DIM	MILLIMETERS						
	MIN	MAX	TYP.	DIM	MIN	MAX	TYP.
A	6.35	6.73	6.54	I	2.19	2.39	2.29
A1	5.22	5.48	5.35	J	0.46	0.62	0.54
B	0.89	1.27	1.08	L	0.46	0.62	0.54
C	6.06	6.44	6.25	M	4.83 MIN.		
E	0.64	1.02	0.83	N	5.21 MIN.		
F	9.65	10.41	10.03	O	2.29 TYP..		2.29
G	0.84	1.14	0.99	Q	0	0.14	0.07
H	0.64	0.90	0.77				

APQ4ESN50AB-XXJ1
TO-252



TO-252 DIMENSION							
DIM	MILLIMETERS						
	MIN	MAX	TYP.	DIM	MIN	MAX	TYP.
A	6.50	6.70	6.60	J	0.46	0.56	0.51
A1	5.12	5.46	5.29	K	2.9 REF		
B	0.89	1.27	1.08	L	0.56	0.46	0.51
C	6.00	6.20	6.10	M	4.83 REF		
E	0.6	1.0	0.80	N	5.35 REF		
F	9.80	10.4	10.00	O	2.19	2.39	2.29
H	0.71	0.81	0.76	Q	0	0.10	0.05
I	2.20	2.38	2.29	R	1.40	1.70	1.55



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500V/4.5A N-Channel MOSFET

Note

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